

# N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
200	0.240 at V <sub>GS</sub> = 10 V	2.2		
	0.260 at V <sub>GS</sub> = 6.0 V	2.1		

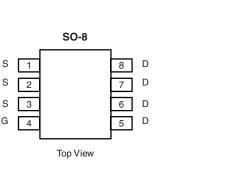
## **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- PWM Optimized for Low  $\mathbf{Q}_{\mathbf{g}}$  and Low  $\mathbf{R}_{\mathbf{g}}$
- Compliant to RoHS Directive 2002/95/EC



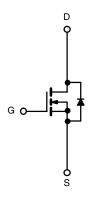
#### **APPLICATIONS**

Primary Side Switch



Ordering Information: Si4464DY-T1-E3 (Lead (Pb)-free)

Si4464DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T <sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	200		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Dusis Comment /T 150 °C\d	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	2.2	1.7	_
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		1.7	1.3	
Pulsed Drain Current		I <sub>DM</sub>	8		Α
Single Avalanch Current	L = 0.1 mH	I <sub>AS</sub>	3		1
Single Avalanch Energy	L = 0.1 11111	E <sub>AS</sub>	0.	45	mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.1	1.2	Α
M	T <sub>A</sub> = 25 °C	D.	2.5	1.5	w
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	- P <sub>D</sub>	1.6	0.9	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manipulation to Applicate	t ≤ 10 s	- R <sub>thJA</sub>	37	50	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		68	85		
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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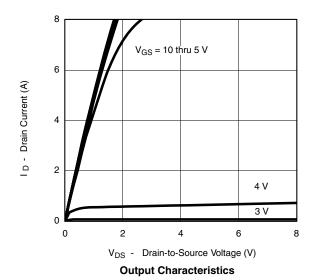
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Cota Valtaga Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V			1	uΑ	
Zero Gate Voltage Drain Current		$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	8			Α	
	В	$V_{GS} = 10 \text{ V}, I_D = 2.2 \text{ A}$		0.195 0.240		0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 6.0 \text{ V}, I_D = 2.1 \text{ A}$		0.210	0.260	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 2.2 \text{ A}$		8.0		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>			1	1			
Total Gate Charge	$Q_g$			12	18		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.2 \text{ A}$		2.5		nC	
Gate-Drain Charge	$Q_{gd}$			3.8			
Gate Resistance	$R_{g}$			2.5		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 100 V, $R_L$ = 100 $\Omega$		12	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$t_{d(off)}$ $I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 6 \Omega$		15	25	ns	
Fall Time	t <sub>f</sub>			15	25		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.1 A, dI/dt = 100 A/μs		60	90		

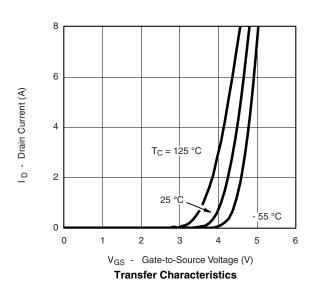
## Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

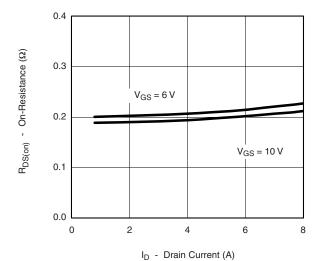




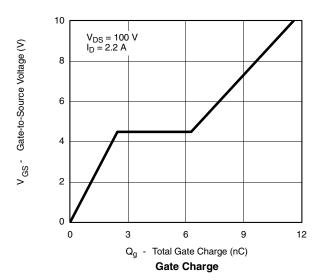


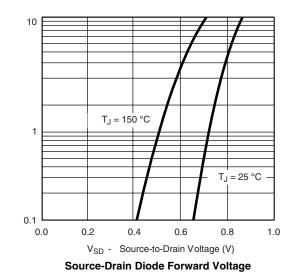


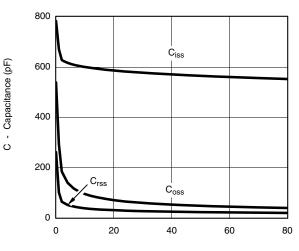
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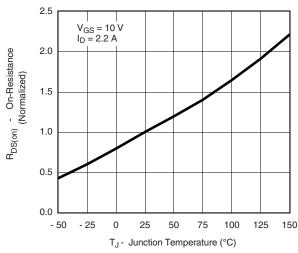
**On-Resistance vs. Drain Current** 



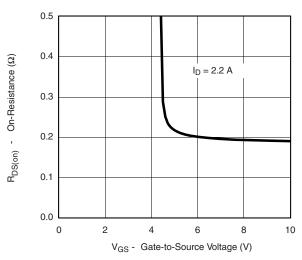




V<sub>DS</sub> - Drain-to-Source V oltage (V) **Capacitance** 



On-Resistance vs. Junction Temperature



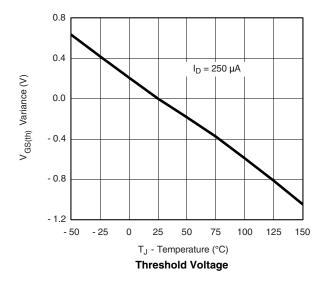
On-Resistance vs. Gate-to-Source Voltage

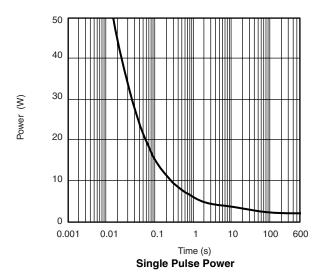
Source Current (A)

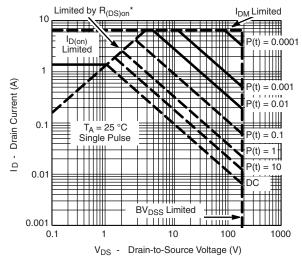
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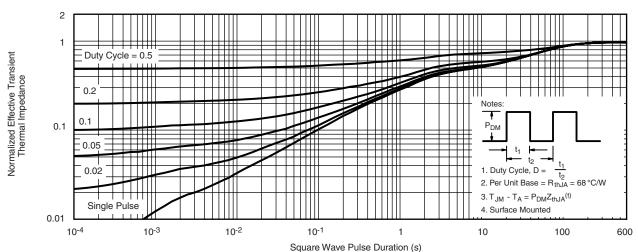






\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified

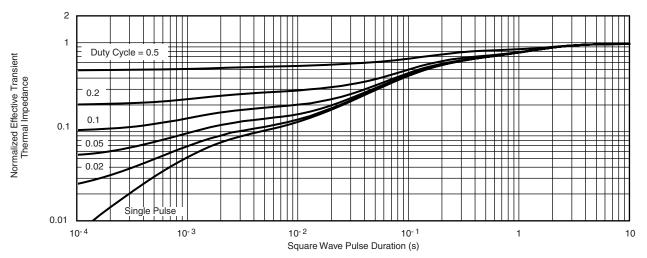
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



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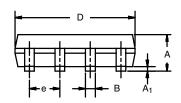
Normalized Thermal Transient Impedance, Junction-to-Foot

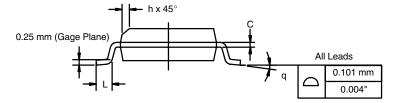
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**SOIC (NARROW): 8-LEAD** JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
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## **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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